

Resolution of Non-Destructive Imaging for Buried Interfaces

A. Hirohata,¹ B. D. Aditya,² J. Wu,² M. Ota,³ K. Elphick,¹ T. Tsuchiya,⁴ T. Ichinose⁴ and S. Mizukami⁴

¹ Department of Electronic Engineering, University of York, York YO10 5DD, United Kingdom

² Department of Electronic Engineering, City University of Hong Kong, Kowloon, Hong Kong S.A.R.

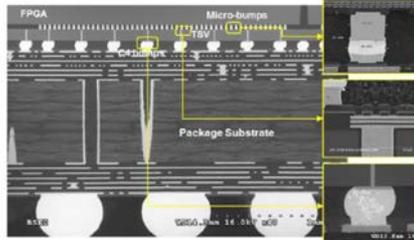
³ Department of Electrical Engineering, Nagaoka University of Technology, Nagaoka 940-2118, Japan

⁴ WPI-Advanced Institute for Materials Research, Tohoku University, Sendai 980-8577, Japan

Cross-sectional image of MRAM



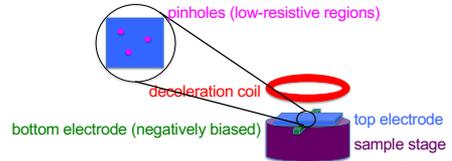
[1] <https://www.everspin.com/>



[2] <http://electroiq.com/insights-from-leading-edge/2014/01/>

- Cross-sectional sample fabrication induced strain.
- Non-destructive evaluation is required.
- Defects should be detected in nm resolution

Aims of this study



Imaging process for buried interfaces : [3]

1. Simulate electron flights in a multilayered structure at a series of decelerated electron-beam.
2. Select representative electron-beam for imaging.
3. Subtract and compare images taken at different electron-beam voltages to highlight any features appeared at each interface.

[3] A. Hirohata et al., Nat. Commun. 7, 12701 (2016).

Sample growth by sputtering (HITUS)

- Ta (5) / Ru (5) / W (0.5) / Ta (5)
- Ta (5) / Ru (5) / W (0.5) / Ta (10)
- Ta (5) / Pt (0.5) / Ta (60)



Tungsten is the heavy metal.

Confirm the resolution of dispersed nano-particle by using non-destructive technique.

CASINO electron flight simulations [4]

- Landing position of an electron is calculated using

$$X_0 = \frac{d\sqrt{\log(R_1)}}{2 \times 1.65} \times \cos(2\pi R_2)$$

$$(0 \leq R \leq 1, \text{ random number})$$

$$Y_0 = \frac{d\sqrt{\log(R_1)}}{2 \times 1.65} \times \cos(2\pi R_3)$$

- For inelastic scattering, the separation between two successive collisions (S) with an electron-beam at E keV can be calculated as

$$E_{i+1} = E_i + \frac{dE}{dS} L$$

$$\frac{dE}{dS} = \frac{-7.85 \times 10^{-3} \rho}{E_i}$$

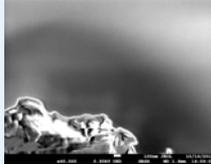
$$\times \sum_{j=1}^n \frac{C_j Z_j}{F_j} \ln \left(1.116 \left(\frac{E_i}{F_j} + k_j \right) \right) [\text{keV/nm}]$$

(C, F, J, k and Z: material constants, ρ: density of a material and L: distance between elastic scattering)

[4] D. Drouin et al., Scanning 29, 92 (2007).

Non-destructive imaging through 5 nm Ta

Acceleration of 0.9 keV :



Acceleration of 1.1 keV :



* Scale : 100 nm, Magnification : 40,000

Subtraction between images taken at 1.0 and 1.2 keV :

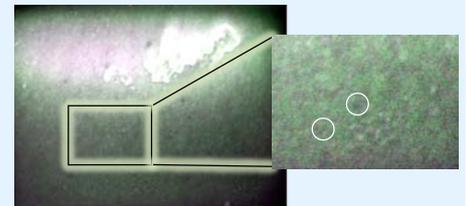


* Scale : 100 nm, Magnification : 40,000

- Maximum particle diameter : 110 nm
- Minimum particle diameter : < 10 nm
- Confirm some dispersed particles.
- Size distributions can be obtained.

Non-destructive imaging through 10 nm Ta

Subtraction between images taken at 1.4 and 1.5 keV :

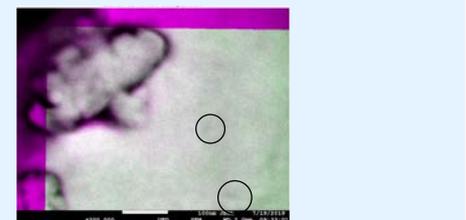


* Scale : 100 nm, Magnification : 70,000

- Maximum particle diameter : 67 nm
- Minimum particle diameter : 6.8 nm

Non-destructive imaging through 60 nm Ta

Subtraction between images taken at 4.7 and 5.0 keV :



* Scale : 100 nm, Magnification : 200,000

- Maximum particle diameter : 36 nm
- Minimum particle diameter : 11 nm

5 nm Ta

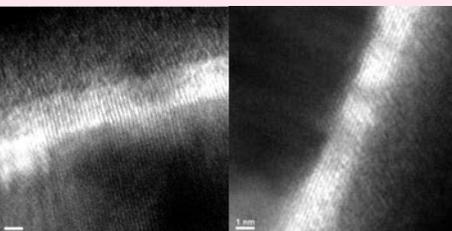
- Electron beam reaches W at 0.9 keV.
- Electron beam reaches bottom of W at 1.1 keV.

10 nm Ta

- Electron beam reaches W at 1.3 keV.
- Electron beam reaches bottom of W at 1.5 keV.

Cross-sectional images

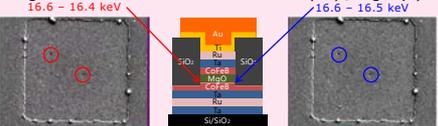
Two distinctive junctions with high and low TMR ratios :



Junction with high TMR ratio Junction with low TMR ratio

Non-destructive images at the bottom interfaces

High TMR – Interface between CoFeB (10) / MgO (2)



Low TMR – Interface between CoFeB (10) / MgO (2)

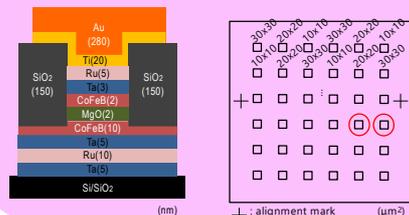


Some pinholes observed only for the high TMR pillars.

Magnetic tunnel junctions

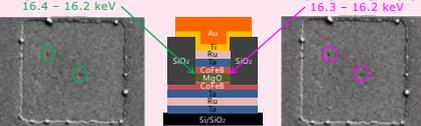
Two distinctive junctions with high and low TMR ratios :

Ta, Ru 100 W, : DC Ar 24.0 sccm (0.10 Pa), RT
 CoFeB 100 W, : DC Ar 24.0 sccm (0.10 Pa), RT
 MgO 50 W, : RF Ar 14.5 sccm (0.06 Pa), RT
 Anneal 500°C, 0 kOe – 500°C, 3 kOe



Non-destructive images at the top interfaces

High TMR – Interface between CoFeB (10) / MgO (2)



Low TMR – Interface between CoFeB (10) / MgO (2)



Some pinholes observed only for the high TMR pillars.

Summary

- We have successfully developed a new non-destructive method to image buried junctions.
- By controlling the electron-beam energy, we have demonstrated the contrast imaging of buried interfaces at a controlled depth.
- We can resolve particles in ~ 7 nm in size below 10 nm thick over layers.